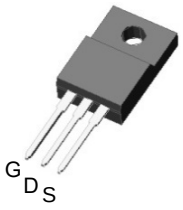
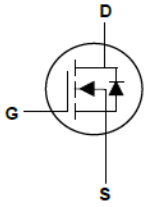
N-Channel Enhancement Mode MOSFET

Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Pin Description

TO-220F	Symbol
	

Applications

- Power Management in Desktop Computer
- DC/DC Converters

V_{DSS}	650	V
$R_{DS(ON)-Typ}$	1100	mΩ
I_D	7	A

Absolute Maximum Ratings(T_J=25℃, Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		650	V
V_{GSS}	Gate-Source Voltage		±30	V
T_J	Maximum Junction Temperature		-55 to 150	℃
T_{STG}	Storage Temperature Range		-55 to 150	℃
E_{AS}	Single Pulse Avalanche Energy[3]		230	mJ
I_{DM} ①	Pulse Drain Current Tested		28	A
I_D	Continuous Drain Current	T_C=25°C	7	A
P_D	Maximum Power Dissipation	T_C=25°C	35	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient[1] （Max）	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	1.98	℃/W

Note ①：Max. current is limited by bonding wire.

Note ②：UIS tested and pulse width are limited by maximum junction temperature 150℃.

Note ③：Surface Mounted on 1in^2 FR-4 board with 1oz.

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Electrical Characteristics (T_J=25℃, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	650	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=650V, V_{GS}=0V	---	---	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	2	---	4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±30V, V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	V_{GS}=10V , I_D=3.5A	---	1100	1300	mΩ
Dynamic Characteristics⑤						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, Freq.=1MHz	---	1098	---	pF
C_{oss}	Output Capacitance		---	93	---	
C_{rss}	Reverse Transfer Capacitance		---	11	---	
$T_{d(on)}$	Turn-on Delay Time	V_{DD}=325V, R_G=25Ω, I_D=7A	---	29	---	nS
T_r	Turn-on Rise Time		---	48	---	
$T_{d(off)}$	Turn-off Delay Time		---	39	---	
T_f	Turn-off Fall Time		---	33	---	
Q_g	Total Gate Charge	V_{DD}=400V , V_{GS}=10V , I_D=7A	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	4	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
Source-Drain Characteristics （T_J=25℃）						
V_{SD}	Diode Forward Voltage②	V_{GS}=0V , I_S=7A ,T_J=25℃	---	---	1.4	V
t_{rr}	Reverse Recovery Time	V_R=400V, I_S=7A, di/dt=100A/μs，T_J=25℃	---	365	---	nS
Q_{rr}	Reverse Recovery Charge		---	3.4	---	nC

Note ④： Pulse test (pulse width≤300us, duty cycle≤2%).

Note ⑤：Guaranteed by design, not subject to production testing.

Typical Characteristics

Figure 1. Output Characteristics

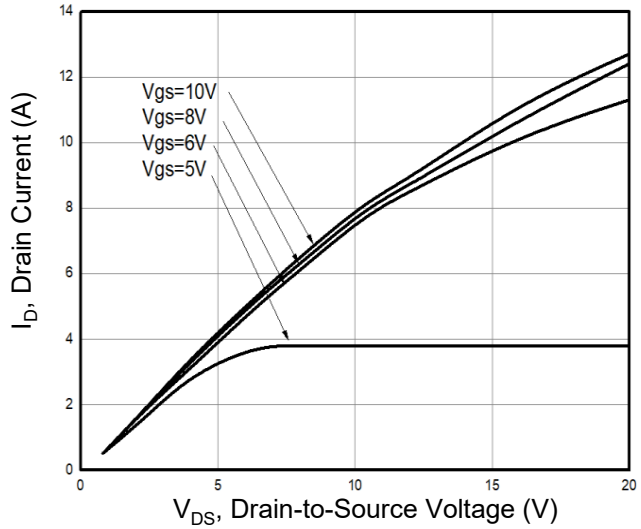


Figure 2. Transfer Characteristics

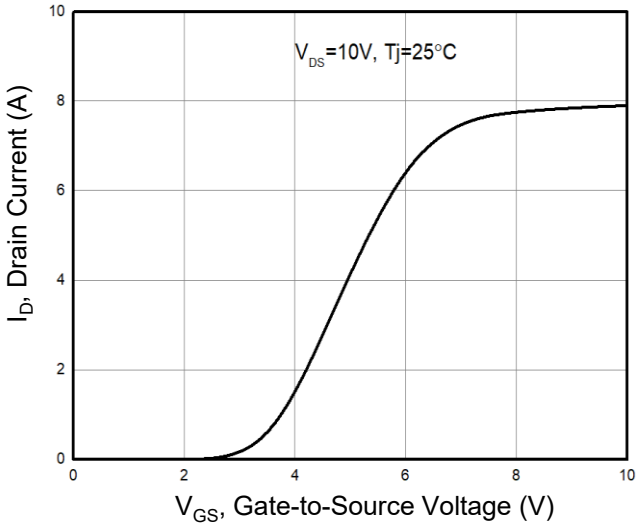


Figure 3. Drain Current vs. Temperature

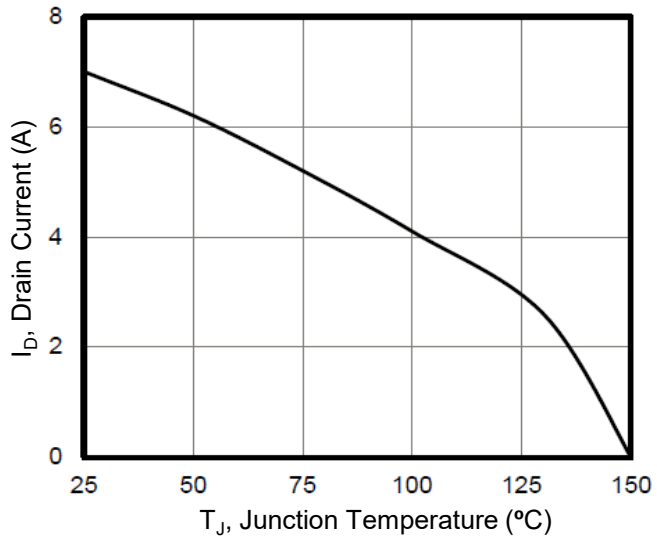


Figure 4. Capacitance

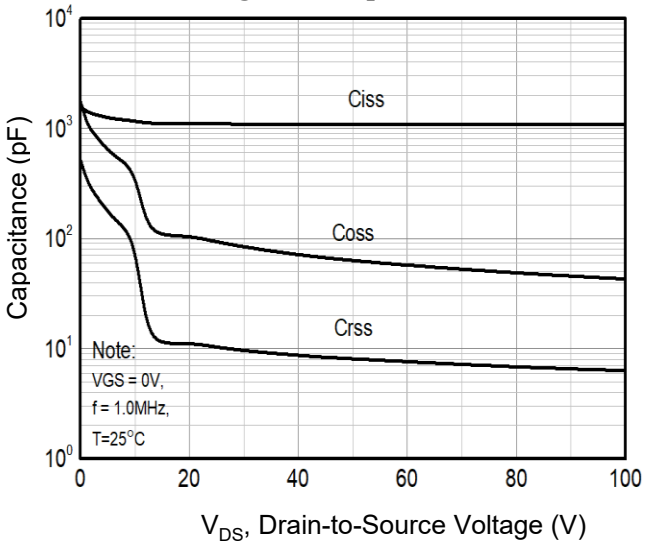


Figure 5. Gate Charge

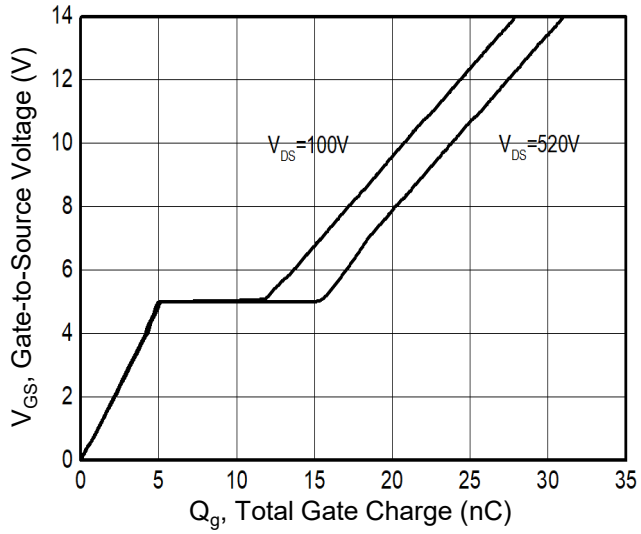


Figure 6. Body Diode Forward Voltage

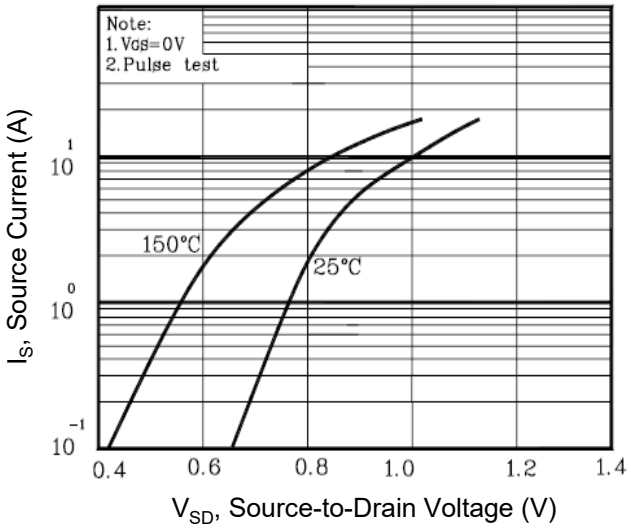


Figure 7. On-Resistance vs. Temperature

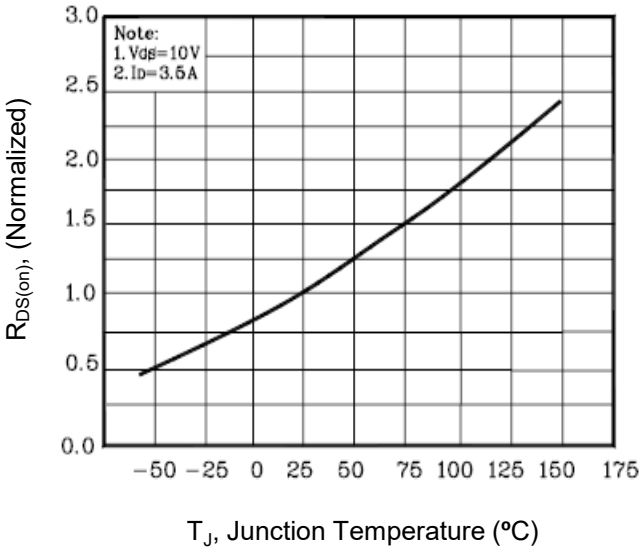


Figure 8. BV_{DSS} vs. Temperature

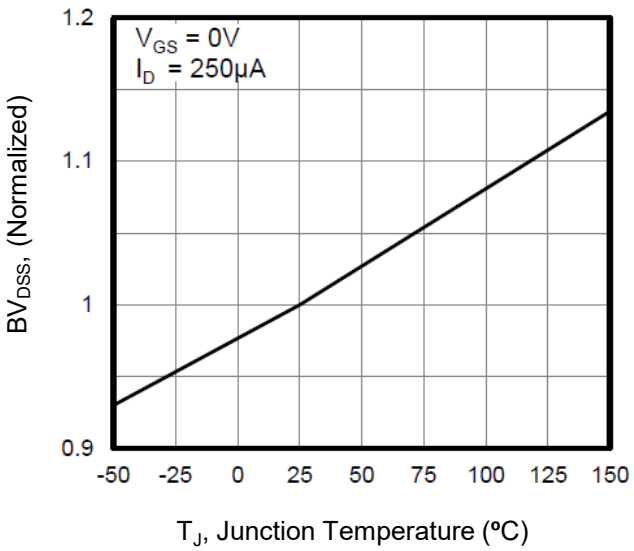


Figure 9. Transient Thermal Impedance (TO-220F)

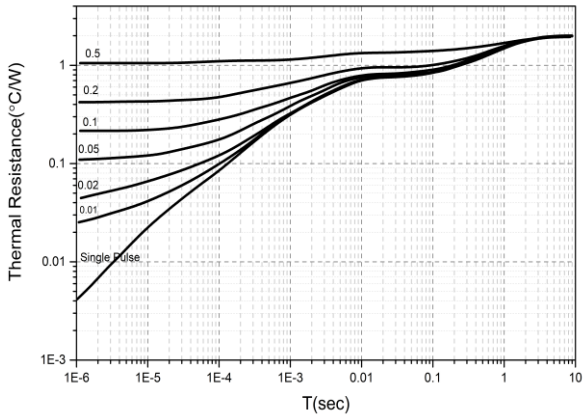
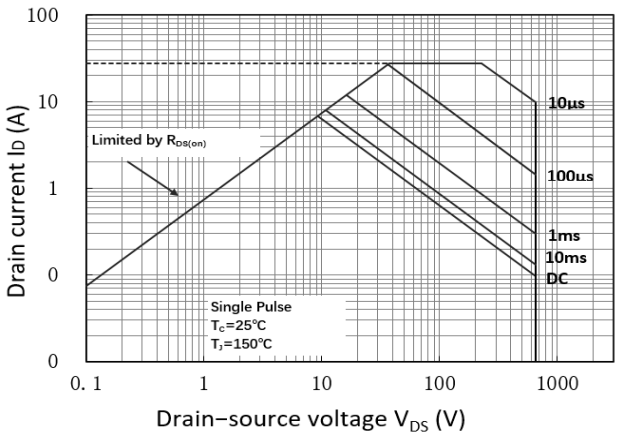


Figure 10. Maximum Safe Operating Area (TO-220F)



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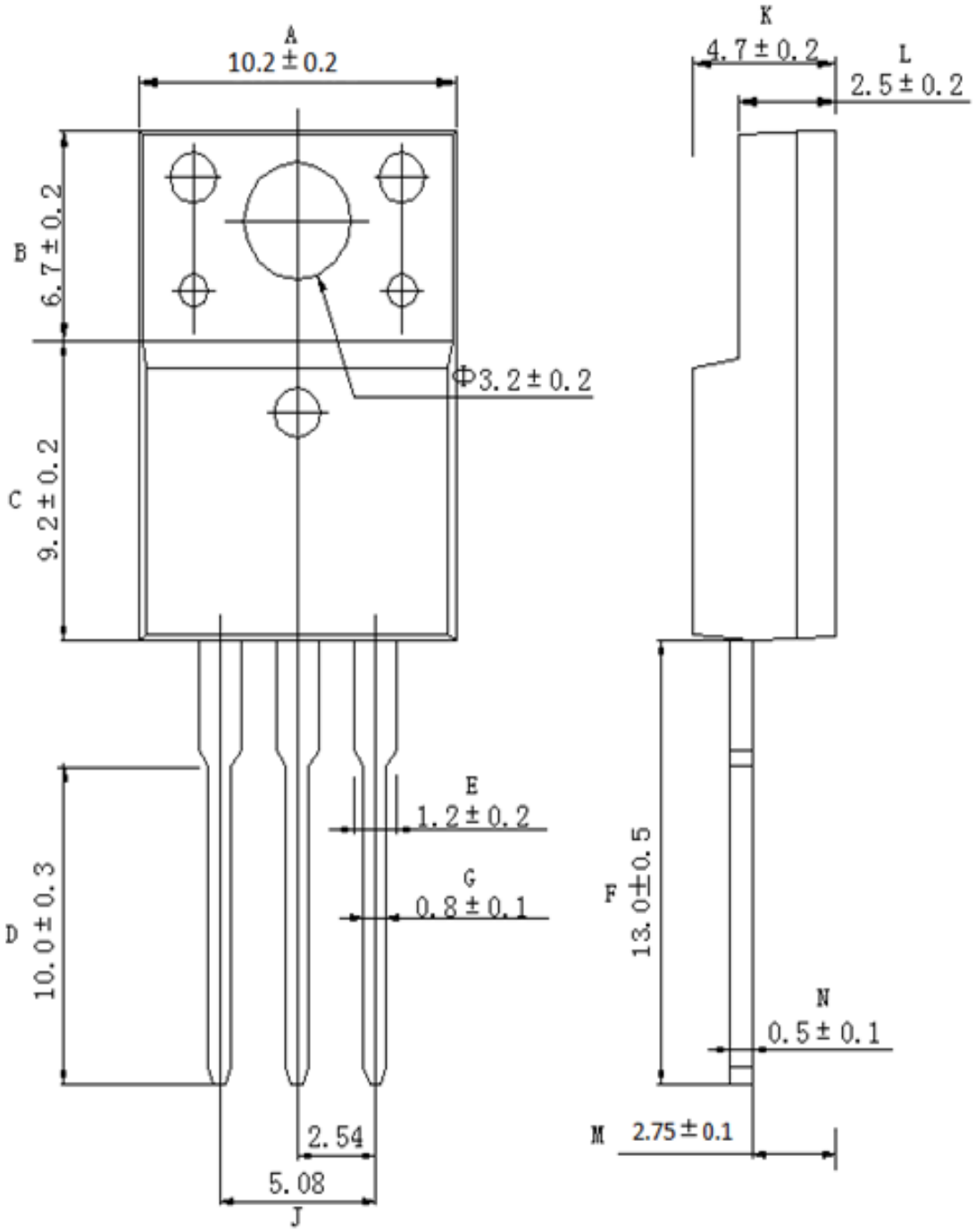
TO-220F Package Outline Data



印字说明

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第一行标记为物料型号代码

第二行为AA为内部识别码，BB为表示年份，例如22即表示2022年，CC表示周期，例如01即表示第一周;2201即表示2022年第一周生产。